EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S2	8	(semiconductor or wafer or substrate) and source and drain and p-type and n-type and (drain near4 drift) and (drain near4 contact) and dop$4 and ((insulat$4 or oxide or dielectric) near4 gate) and channel and strip$4 and voltage and localis$4 and (trench or via of hole) and deplet$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 14:17
S3	22505	(localize$4 near4 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:16
S4	1	(localize$4 near4 region) near9 (drain near drift)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:17
S5	286	(localize$4 near4 region) near9 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:17
S6	67	(localize$4 near4 region) near9 drain near9 channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:17
S7	1	(localize$4 near4 region) near9 drain near9 channel and (alternat$4 near9 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:18
S8	1	(localize$4 near4 region) near9 drain near9 channel and (alternat$4 near9 (conductivity or npn or pnp))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:18

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S9	257	(semiconductor or wafer or substrate) and source and drain and p-type and n-type and (drain near4 drift) and (drain near4 contact) and dop$4 and ((insulat$4 or oxide or dielectric) near4 gate) and channel and strip$4 and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 10:04
S10	2	(semiconductor or wafer or substrate) and source and drain and p-type and n-type and (drain near4 drift) and (drain near4 contact) and dop$4 and ((insulat$4 or oxide or dielectric) near4 gate) and channel and strip$4 and voltage and (438/301.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 10:11
S11	6	(semiconductor or wafer or substrate) and source and drain and p-type and n-type and (drain near4 drift) and (drain near4 contact) and dop$4 and ((insulat$4 or oxide or dielectric) near4 gate) and channel and strip$4 and voltage and (257/288.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/03 10:13